

PATENT**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Yi-Fan Chen, Examiner: Huynh, Andy
Chi-King Pu,
Shou-Kong Fan

Filing Date: 04/18/01

Art Unit: 2818

Serial No.: 09/836,258

Docket No.: NAUP0280USA

10 Title: BYPASS CIRCUITS FOR REDUCING PLASMA DAMAGE

To: The Commissioner of Patents and Trademarks
Washington, D.C. 20231

15 Subject: Response to the Office Action dated 05/03/2002

Dear Sir:

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JUL 11 2002

TECHNOLOGY CENTER 2800

AMENDMENT

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In response to the Office Action identified above,
please amend the above-identified application as
follows:

25 In the claims:

1. (Once amended) A bypass circuit for reducing plasma
damage to a gate oxide of a metal-oxide semiconductor
(MOS) wafer, the bypass circuit positioned on a
semiconductor wafer, the semiconductor wafer
comprising a substrate, the MOS transistor, a
dielectric layer, and the bypass circuit, respectively,
with the bypass circuit comprising:

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